a plurality of first conductive type semiconductor regions reaching said semiconductor substrate from a surface of said first semiconductor layer, said first conductive type semiconductor regions being formed apart from each other;

a second conductive type semiconductor region selectively formed on the surface of said first semiconductor layer, said second conductive type semiconductor region surrounding each of said first conductive type semiconductor regions with a portion of said first semiconductor layer therebetween;

a first electrode formed on said second conductive type semiconductor region; and

a second electrode formed on said second surface of said semiconductor substrate;

said portion of said first semiconductor layer between each of said first conductive type semiconductor regions and said second conductive type semiconductor region having a higher resistance than resistances of said first conductive type semiconductor regions and said second conductive type semiconductor region.

2. (Amended) The semiconductor light-receiving device according to claim 1, wherein said second conductive type semiconductor region has a lattice form or a network form.

3. (Amended) The semiconductor light-receiving device according to claim 2, wherein said first electrode has the lattice form or the network form and is provided on said second conductive type semiconductor region.

4. (Amended) The semiconductor light-receiving device according to claim 1, wherein said first electrode is formed on part of said second conductive type semiconductor region.

5. (Amended) The semiconductor light-receiving device according to claim 1, wherein each of said first conductive type semiconductor regions has an island form or a stripe form.

6. (Amended) The semiconductor light-receiving device according to claim 1, wherein the portion of said first semiconductor layer between said second conductive type semiconductor region and each of said first conductive type semiconductor layers is completely depleted in a state in which a reverse bias is applied between said first electrode and said second electrode.

7. (Amended) A semiconductor light-receiving device comprising:

a first conductive type semiconductor substrate having a first surface on a light-receiving side and a second surface on the opposite side to said first surface;

a first semiconductor layer formed on said first surface of said semiconductor substrate;

a plurality of first conductive type semiconductor regions reaching said semiconductor substrate from a surface of said first semiconductor layer, said first conductive type semiconductor regions being formed apart from each other;

a second conductive type semiconductor region selectively formed on the surface of said first semiconductor layer and having a plurality of openings, each of said first conductive type semiconductor regions being provided within each of said openings of said second conductive type semiconductor region respectively with a portion of said first semiconductor layer therebetween;

a first electrode formed on said second conductive type semiconductor region; and

a second electrode formed on said second surface of said semiconductor substrate;

said portion of said first semiconductor layer between each of said first conductive type semiconductor regions and said second conductive type semiconductor region has a higher resistance than resistances of said first conductive type semiconductor regions and said second conductive type semiconductor region.

8. (Amended) The semiconductor light-receiving device according to claim 7, wherein said first electrode has a lattice form or a network form and is provided on said second conductive type semiconductor region.

9. (Amended) The semiconductor light-receiving device according to claim 7, wherein said first electrode is formed on part of said second conductive type semiconductor region.

10. (Amended) The semiconductor light-receiving device according to claim 7, wherein each of said first conductive type semiconductor regions has an island form or a stripe form.

11. (Amended) The semiconductor light-receiving device according to claim 7, wherein the portion of said first semiconductor layer between said second conductive type semiconductor region and each of said first conductive type semiconductor regions is completely depleted in a state in which a reverse bias is applied between said first electrode and said second electrode.

12. (Amended) A semiconductor light-receiving device comprising:

a first conductive type semiconductor substrate having a first surface on a light-receiving side and a second surface on the opposite side to said first surface, said first surface including a plurality of protruded surface portions separated from each other;

a first semiconductor layer selectively formed on said first surface of said semiconductor substrate, said first semiconductor layer having a higher resistance than a

resistance of said semiconductor substrate and having a plurality of openings, each of said protruded surface portions of said first surface being exposed within each of said openings of said first semiconductor layer respectively;

a second conductive type semiconductor region selectively formed on a surface of said first semiconductor layer and surrounding each of said protruded surface portions of said first surface with a portion of said first semiconductor layer therebetween;

a first electrode formed on said second conductive type semiconductor region; and

a second electrode formed on said second surface of said semiconductor substrate.

13. (Amended) The semiconductor light-receiving device according to claim 12, wherein said second conductive type semiconductor region has a lattice form or a network form.

14. (Amended) The semiconductor light-receiving device according to claim 13, wherein said first electrode has the lattice form or the network form and is provided on said second conductive type semiconductor region.

15. (Amended) The semiconductor light-receiving device according to claim 12, wherein said first electrode is formed on part of said second conductive type semiconductor region.

17. (Amended) The semiconductor light-receiving device according to claim 12, wherein said portion of said first semiconductor layer between said second conductive type semiconductor layer and each of said protruded surface portions of said semiconductor substrate is completely depleted in a state in which a reverse bias is applied between said first electrode and said second electrode.

18. (Amended) A semiconductor light-receiving device comprising:

a first conductive type semiconductor substrate having a first surface on a light-receiving side and a second surface on the opposite side to said first surface, said first surface including a plurality of protruded surface portions separated from each other;

a first semiconductor layer selectively formed on said first surface of said semiconductor substrate, said first semiconductor layer having a higher resistance than a resistance of said semiconductor substrate and having a plurality of openings, each of said protruded surface portions of said first surface being exposed within each of said openings of said first semiconductor layer respectively;

a second conductive type semiconductor region selectively formed on a surface of said first semiconductor layer and having a plurality of openings, each of said protruded surface portions of said first surface being provided within each of said openings of said second conductive type semiconductor region respectively with a portion of said first semiconductor layer therebetween;

a first electrode formed on said second conductive type semiconductor region; and

a second electrode formed on said second surface of said semiconductor substrate.

19. (Amended) The semiconductor light-receiving device according to claim 18, wherein said first electrode has a lattice form or a network form and is provided on said second conductive type semiconductor region.

20. (Amended) The semiconductor light-receiving device according to claim 18, wherein said first electrode is formed on part of said second conductive type semiconductor region.

22. (Amended) The semiconductor light-receiving device according to claim 18, wherein said portion of said first semiconductor layer between said second conductive type semiconductor region and each of said protruded surface portions of said semiconductor